



**MOTOROLA**

**MC14551B**

**QUAD 2-CHANNEL  
ANALOG MULTIPLEXER/DEMULTIPLEXER**

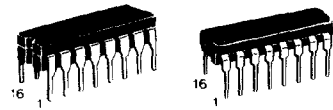
The MC14551B is a digitally-controlled analog switch. This device implements a 4PDT solid state switch with low ON impedance and very low OFF Leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Analog Voltage Range ( $V_{DD}-V_{EE}$ ) = 3 to 18 V  
Note:  $V_{EE}$  must be  $\leq V_{SS}$
- Linearized Transfer Characteristics
- Low Noise —  $12 \text{ nV}/\sqrt{\text{Cycle}}$ ,  $f \geq 1 \text{ kHz}$  typical
- For Lower  $R_{ON}$ , Use The HC4051, HC4052, or HC4053 High-Speed CMOS Devices

**CMOS MSI**

(LOW-POWER COMPLEMENTARY MOS)

**ANALOG MULTIPLEXER/  
DEMULTIPLEXER**



CASE 620  
L SUFFIX  
CERAMIC PACKAGE

CASE 648  
P SUFFIX  
PLASTIC PACKAGE

**MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage (Referenced to $V_{EE}$ , $V_{SS} \approx V_{EE}$ )	- 0.5 to +18.0	V
$V_{in}, V_{out}$	Input or Output Voltage (DC or Transient) (Referenced to $V_{SS}$ for Control Input & $V_{EE}$ for Switch I/O)	- 0.5 to $V_{DD} + 0.5$	V
$I_{in}$	Input Current (DC or Transient), per Control Pin	$\pm 10$	mA
$I_{sw}$	Switch Through Current	$\pm 25$	mA
$P_D$	Power Dissipation, per Package†	500	mW
$T_{stg}$	Storage Temperature	- 65 to +150	°C
$T_L$	Lead Temperature (8-Second Soldering)	260	°C

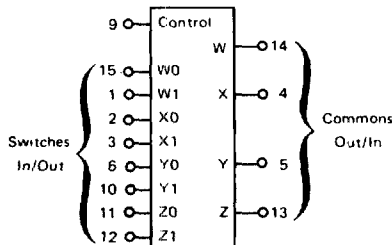
\*Maximum Ratings are those values beyond which damage to the device may occur.  
†Temperature Derating: Plastic "P" Package: - 12mW/°C from 65°C to 85°C  
Ceramic "L" Package: - 12mW/°C from 100°C to 125°C

**ORDERING INFORMATION**

A Series: - 55°C to +125°C  
MC14XXXBAL (Ceramic Package Only)

C Series: - 40°C to +85°C  
MC14XXXBCP (Plastic Package)  
MC14XXXBCL (Ceramic Package)

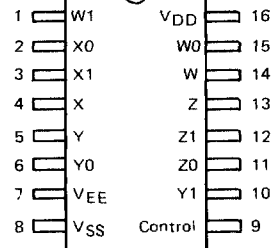
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Control	ON
0	W0 X0 Y0 Z0
1	W1 X1 Y1 Z1

$V_{DD}$  = Pin 16  
 $V_{SS}$  = Pin 8  
 $V_{EE}$  = Pin 7

**PIN ASSIGNMENT**



Note: Control Input referenced to  $V_{SS}$ , Analog Inputs and Outputs reference to  $V_{EE}$ .  $V_{EE}$  must be  $\leq V_{SS}$

# MC14551B

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	V <sub>DD</sub>	Test Conditions	T <sub>low</sub> *		25°C			T <sub>high</sub> *		Unit
				Min	Max	Min	Typ#	Max	Min	Max	
<b>SUPPLY REQUIREMENTS</b> (Voltages Referenced to V <sub>EE</sub> )											
Power Supply Voltage Range	V <sub>DD</sub>	—	V <sub>DD</sub> - 3 ≥ V <sub>SS</sub> ≥ V <sub>EE</sub>	3	18	3	—	18	3	18	V
Quiescent Current Per Package (AL Device)	I <sub>DD</sub>	5	Control Inputs: V <sub>in</sub> = V <sub>SS</sub> or V <sub>DD</sub> , Switch I/O: V <sub>EE</sub> ≤ V <sub>I/O</sub> ≤ V <sub>DD</sub> , and ΔV <sub>switch</sub> ≤ 500 mV**	—	5	—	0.005	5	—	150	μA
		10		—	10	—	0.010	10	—	300	
		15		—	20	—	0.015	20	—	600	
Quiescent Current Per Package (CL/CP Device)	I <sub>DD</sub>	5	Control Inputs: V <sub>in</sub> = V <sub>SS</sub> or V <sub>DD</sub> , Switch I/O: V <sub>EE</sub> ≤ V <sub>I/O</sub> ≤ V <sub>DD</sub> , and ΔV <sub>switch</sub> ≤ 500 mV**	—	20	—	0.005	20	—	150	μA
		10		—	40	—	0.010	40	—	300	
		15		—	80	—	0.015	80	—	600	
Total Supply Current (Dynamic Plus Quiescent, Per Package)	I <sub>D(AV)</sub>	5 10 15	T <sub>A</sub> = 25°C only (The channel component, (V <sub>in</sub> - V <sub>out</sub> )/R <sub>on</sub> , is not included.)	Typical (0.07 μA/kHz)f + I <sub>DD</sub> (0.20 μA/kHz)f + I <sub>DD</sub> (0.36 μA/kHz)f - I <sub>DD</sub>						μA	

## CONTROL INPUT

 (Voltages Referenced to V<sub>SS</sub>)

Low-Level Input Voltage	V <sub>IL</sub>	5	R <sub>on</sub> = per spec, I <sub>off</sub> = per spec	—	1.5	—	2.25	1.5	—	1.5	V
		10		—	3.0	—	4.50	3.0	—	3.0	
		15		—	4.0	—	6.75	4.0	—	4.0	
High-Level Input Voltage	V <sub>IH</sub>	5	R <sub>on</sub> = per spec, I <sub>off</sub> = per spec	3.5	—	3.5	2.75	—	3.5	—	V
		10		7.0	—	7.0	5.50	—	7.0	—	
		15		11.0	—	11.0	8.25	—	11.0	—	
Input Leakage Current (AL Device)	I <sub>in</sub>	15	V <sub>in</sub> = 0 or V <sub>DD</sub>	—	±0.1	—	±0.00001	±0.1	—	±1.0	μA
Input Leakage Current (CL/CP Device)	I <sub>in</sub>	15	V <sub>in</sub> = 0 or V <sub>DD</sub>	—	±0.3	—	±0.00001	±0.3	—	±1.0	μA
Input Capacitance	C <sub>in</sub>	—		—	—	—	5.0	7.5	—	—	pF

## SWITCHES IN/OUT AND COMMONS OUT/IN - W, X, Y, Z

 (Voltages Referenced to V<sub>EE</sub>)

Recommended Peak-to-Peak Voltage Into or Out of the Switch	V <sub>I/O</sub>	—	Channel On or Off	0	V <sub>DD</sub>	0	—	V <sub>DD</sub>	0	V <sub>DD</sub>	V <sub>p-p</sub>
Recommended Static or Dynamic Voltage Across the Switch** (Figure 3)	ΔV <sub>switch</sub>	—	Channel On	0	600	0	—	600	0	300	mV
Output Offset Voltage	V <sub>OO</sub>	—	V <sub>in</sub> = 0 V, No load	—	—	—	10	—	—	—	μV
ON Resistance (AL Device)	R <sub>on</sub>	5	ΔV <sub>switch</sub> ≤ 500 mV**, V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> (Control), and V <sub>in</sub> = 0 to V <sub>DD</sub> (Switch)	—	800	—	250	1050	—	1300	Ω
		10		—	400	—	120	500	—	550	
		15		—	220	—	80	280	—	320	
ON Resistance (CL/CP Device)	R <sub>on</sub>	5	ΔV <sub>switch</sub> ≤ 500 mV**, V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> (Control), and V <sub>in</sub> = 0 to V <sub>DD</sub> (Switch)	—	880	—	250	1050	—	1200	Ω
		10		—	450	—	120	500	—	520	
		15		—	250	—	80	280	—	300	
Δ ON Resistance Between Any Two Channels in the Same Package	ΔR <sub>on</sub>	5		—	70	—	25	70	—	135	Ω
		10		—	50	—	10	50	—	95	
		15		—	45	—	10	45	—	65	
Off-Channel Leakage Current (AL Device) (Figure 8)	I <sub>off</sub>	15	V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> (Control) Channel to Channel or Any One Channel	—	±100	—	±0.05	±100	—	±1000	nA
Off-Channel Leakage Current (CL/CP Device) (Figure 8)	I <sub>off</sub>	15	V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> (Control) Channel to Channel or Any One Channel	—	±300	—	±0.05	±300	—	±1000	nA
Capacitance, Switch I/O	C <sub>I/O</sub>	—	Switch Off	—	—	—	10	—	—	—	pF
Capacitance, Common O/I	C <sub>O/I</sub>	—		—	—	—	17	—	—	—	pF
Capacitance, Feedthrough (Channel Off)	C <sub>I/O</sub>	—	Pins Not Adjacent	—	—	—	0.15	—	—	—	pF
		—	Pins Adjacent	—	—	—	0.47	—	—	—	

\* T<sub>low</sub> = -55°C for AL Device, -40°C for CL/CP Device.

T<sub>high</sub> = +125°C for AL Device, +85°C for CL/CP Device.

# Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.

\*\* For voltage drops across the switch (ΔV<sub>switch</sub>) > 600 mV (> 300 mV at high temperature), excessive V<sub>DD</sub> current may be drawn: i.e. the current out of the switch may contain both V<sub>DD</sub> and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

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## ELECTRICAL CHARACTERISTICS ( $C_L = 50$ pF, $T_A = 25^\circ\text{C}$ , $V_{EE} \leq V_{SS}$ )

Characteristic	Symbol	$V_{DD} - V_{EE}$ $V_{dc}$	Min	Typ #	Max	Unit
Propagation Delay Times Switch Input to Switch Output ( $R_L = 10$ k $\Omega$ ) $t_{PLH}, t_{PHL} = (0.17$ ns/pF) $C_L + 26.5$ ns $t_{PLH}, t_{PHL} = (0.08$ ns/pF) $C_L + 11$ ns $t_{PLH}, t_{PHL} = (0.06$ ns/pF) $C_L + 9.0$ ns	$t_{PLH}, t_{PHL}$	5.0 10 15	— — —	35 15 12	90 40 30	ns
Control Input to Output ( $R_L = 10$ k $\Omega$ ) $V_{EE} = V_{SS}$ (Figure 4)	$t_{PLH}, t_{PHL}$	5.0 10 15	— — —	350 140 100	875 350 250	ns
Second Harmonic Distortion $R_L = 10$ k $\Omega$ , $f = 1$ kHz, $V_{in} = 5$ V <sub>p-p</sub>	—	10	—	0.07	—	%
Bandwidth (Figure 5) $R_L = 1$ k $\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p $20 \log \frac{V_{out}}{V_{in}} = -3$ dB, $C_L = 50$ pF	BW	10	—	17	—	MHz
Off Channel Feedthrough Attenuation, Figure 5 $R_L = 1$ k $\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p $f_{in} = 55$ MHz	—	10	—	-50	—	dB
Channel Separation (Figure 6) $R_L = 1$ k $\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p $f_{in} = 3$ MHz	—	10	—	-50	—	dB
Crosstalk, Control Input to Common O/I, Figure 7 $R1 = 1$ k $\Omega$ , $R_L = 10$ k $\Omega$ , Control $t_r = t_f = 20$ ns	—	10	—	75	—	mV

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$  for control inputs and  $V_{EE} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$  for Switch I/O.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$ ,  $V_{EE}$ , or  $V_{DD}$ ). Unused outputs must be left open.

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FIGURE 1 – SWITCH CIRCUIT SCHEMATIC

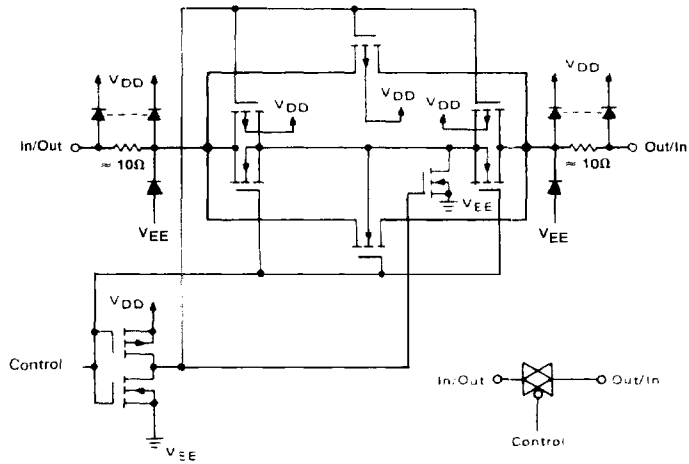
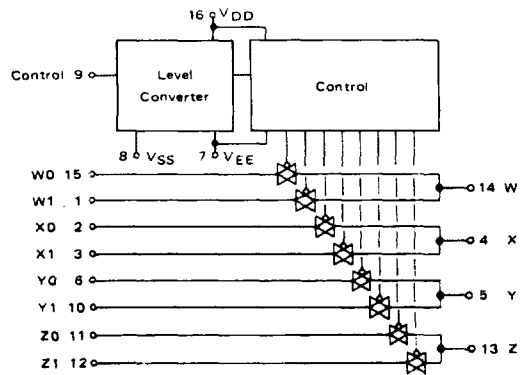


FIGURE 2 – MC14551B FUNCTIONAL DIAGRAM



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## TEST CIRCUITS

FIGURE 3 —  $\Delta V$  ACROSS SWITCH

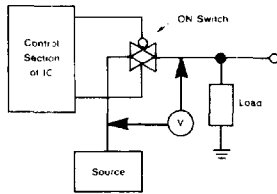


FIGURE 4 — PROPAGATION DELAY TIMES, CONTROL TO OUTPUT

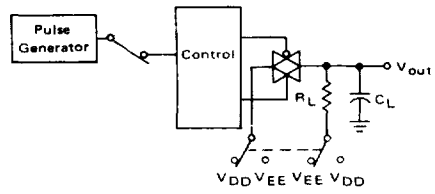


FIGURE 5 — BANDWIDTH AND OFF-CHANNEL FEEDTHROUGH ATTENUATION

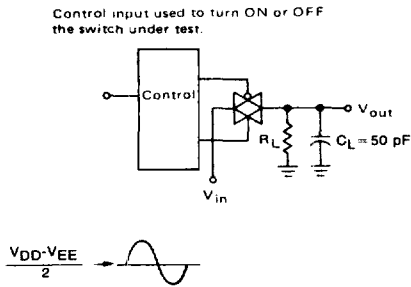


FIGURE 6 — CHANNEL SEPARATION (Adjacent Channels Used for Setup)

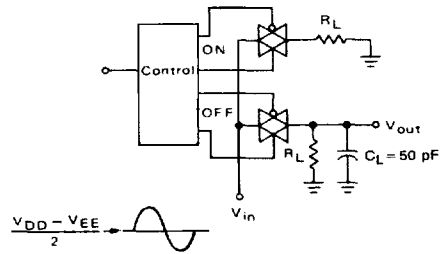


FIGURE 7 — CROSSTALK, CONTROL INPUT TO COMMON O/I

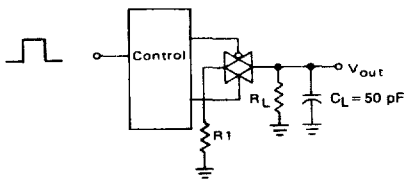
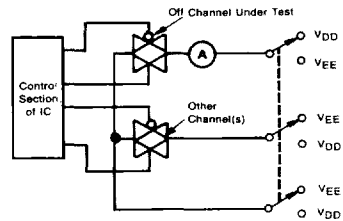
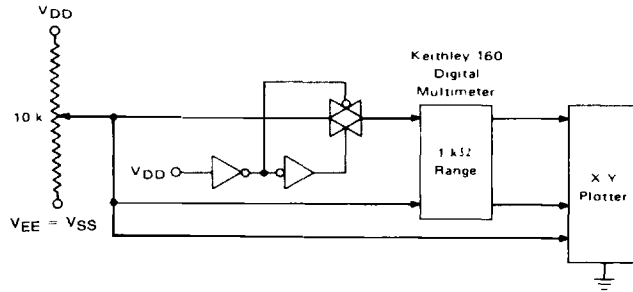


FIGURE 8 — OFF CHANNEL LEAKAGE



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FIGURE 9 – CHANNEL RESISTANCE ( $R_{ON}$ ) TEST CIRCUIT



## TYPICAL RESISTANCE CHARACTERISTICS

FIGURE 10 –  $V_{DD}$  @ 7.5 V,  $V_{EE}$  @ -7.5 V

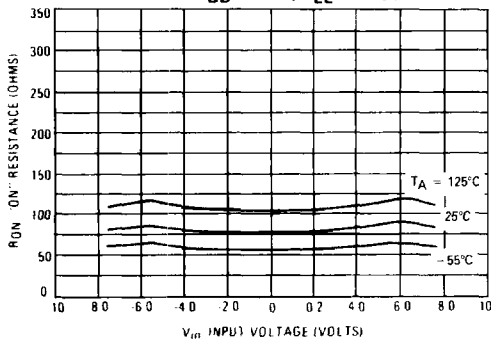


FIGURE 11 –  $V_{DD}$  @ 5.0 V,  $V_{EE}$  @ -5.0 V

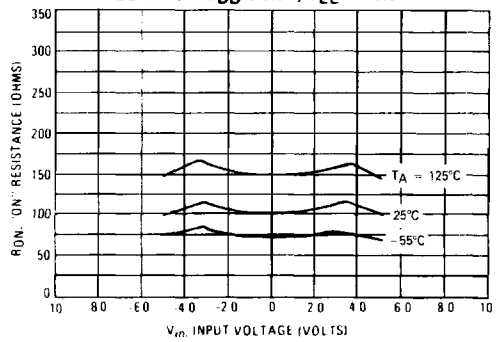


FIGURE 12 –  $V_{DD}$  @ 2.5 V,  $V_{EE}$  @ -2.5 V

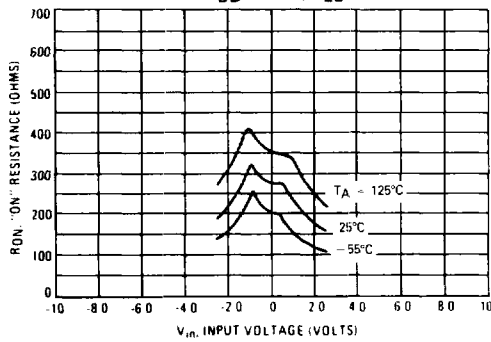
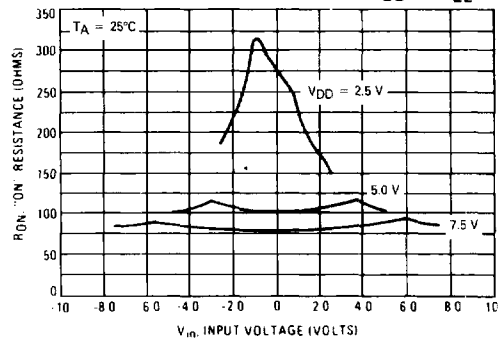


FIGURE 13 – COMPARISON at  $25^\circ\text{C}$ ,  $V_{DD}$  @  $-V_{EE}$



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## APPLICATIONS INFORMATION

Figure A illustrates use of the on-chip level converter detailed in Figure 2. The 0-to-5 volt Digital Control signal is used to directly control a 9 V<sub>p-p</sub> analog signal.

The digital control logic levels are determined by V<sub>DD</sub> and V<sub>SS</sub>. The V<sub>DD</sub> voltage is the logic high voltage; the V<sub>SS</sub> voltage is logic low. For the example, V<sub>DD</sub> = +5 V = logic high at the control inputs; V<sub>SS</sub> = GND = 0 V = logic low.

The maximum analog signal level is determined by V<sub>DD</sub> and V<sub>EE</sub>. The V<sub>DD</sub> voltage determines the maximum recommended peak above V<sub>SS</sub>. The V<sub>EE</sub> voltage determines the maximum swing below V<sub>SS</sub>. For the example, V<sub>DD</sub> - V<sub>SS</sub> = 5 volt maximum swing above V<sub>SS</sub>; V<sub>SS</sub> - V<sub>EE</sub> = 5 volt maximum swing

below V<sub>SS</sub>. The example shows a ±4.5 volt signal which allows a 1/2 volt margin at each peak. If voltage transients above V<sub>DD</sub> and/or below V<sub>EE</sub> are anticipated on the analog channels, external diodes (D<sub>x</sub>) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The absolute maximum potential difference between V<sub>DD</sub> and V<sub>EE</sub> is 18.0 volts. Most parameters are specified up to 15 volts which is the recommended maximum difference between V<sub>DD</sub> and V<sub>EE</sub>.

Balanced supplies are not required. However, V<sub>SS</sub> must be greater than or equal to V<sub>EE</sub>. For example, V<sub>DD</sub> = +10 volts, V<sub>SS</sub> = +5 volts, and V<sub>EE</sub> = -3 volts is acceptable. See the table below.

FIGURE A — APPLICATION EXAMPLE

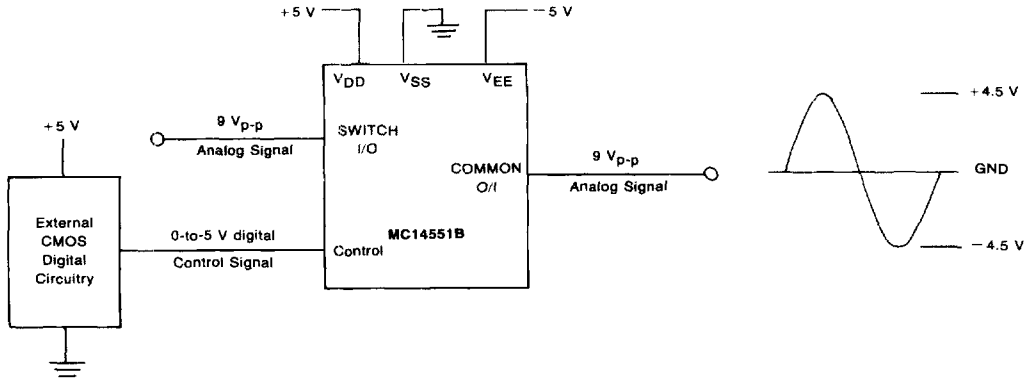
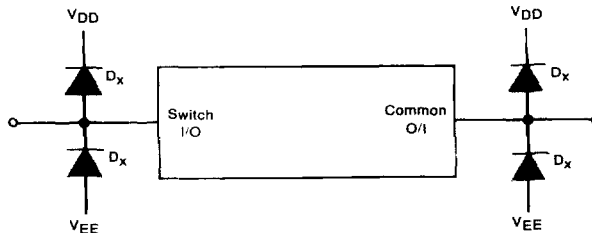


FIGURE B — EXTERNAL SCHOTTKY OR GERMANIUM CLIPPING DIODES



### POSSIBLE SUPPLY CONNECTIONS

V <sub>DD</sub> In Volts	V <sub>SS</sub> In Volts	V <sub>EE</sub> In Volts	Control Inputs Logic High/Logic Low In Volts	Maximum Analog Signal Range In Volts
+8	0	-8	+8/0	+8 to -8 = 16 V <sub>p-p</sub>
+5	0	-12	+5/0	+5 to -12 = 17 V <sub>p-p</sub>
+5	0	0	+5/0	+5 to 0 = 5 V <sub>p-p</sub>
+5	0	-5	+5/0	+5 to -5 = 10 V <sub>p-p</sub>
+10	+5	-5	+10/+5	+10 to -5 = 15 V <sub>p-p</sub>